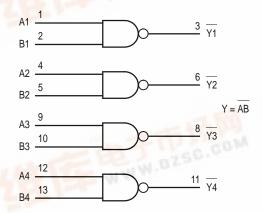
Quad 2-Input NAND Gate

The MC74VHC00 is an advanced high speed CMOS 2–input NAND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: tpD = 3.7ns (Typ) at VCC = 5V
- Low Power Dissipation: ICC = 2μA (Max) at TA = 25°C
- High Noise Immunity: VNIH = VNIL = 28% VCC
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: VOLP = 0.8V (Max)
- · Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 32 FETs or 8 Equivalent Gates

LOGIC DIAGRAM



Pinout: 14-Lead Packages (Top View)



MC74VHC00



D SUFFIX 14-LEAD SOIC PACKAGE CASE 751A-03



DT SUFFIX 14-LEAD TSSOP PACKAGE CASE 948G-01



M SUFFIX 14-LEAD SOIC EIAJ PACKAGE CASE 965-01

ORDERING INFORMATION

MC74VHCXXD SOIC
MC74VHCXXDT TSSOP
MC74VHCXXM SOIC EIAJ

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	H
Н	Н	L CO



MC74VHC00

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage	- 0.5 to + 7.0	V
V _{out}	DC Output Voltage	- 0.5 to V _{CC} + 0.5	V
lικ	Input Diode Current	- 20	mA
lok	Output Diode Current	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V_{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
VCC	DC Supply Voltage	2.0	5.5	V	
V _{in}	DC Input Voltage	0	5.5	V	
V _{out}	DC Output Voltage	0	Vcc	V	
TA	Operating Temperature, All Package T	- 40	+ 85	°C	
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	0 0	100 20	ns/V

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or VCC). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS

			VCC		T _A = 25°C	;	$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
VIH	High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V
VIL	Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	٧
VOH	High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OH} = – 50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $I_{\text{OH}} = -4\text{mA}$ $I_{\text{OH}} = -8\text{mA}$	3.0 4.5	2.58 3.94			2.48 3.80		
VOL	Low–Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $I_{OL} = 50\mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH}$ or V_{IL} $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44	

DC ELECTRICAL CHARACTERISTICS

			v _{CC}	T _A = 25°C		T _A = -40 to 85°C			
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
l _{in}	Input Leakage Current	V _{in} = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
ICC	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			2.0		20.0	μА

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns)

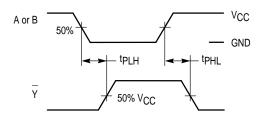
				T _A = 25°C		T _A = - 40 to 85°C			
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagat <u>io</u> n Delay, A or B to Y	$V_{CC} = 3.3 \pm 0.3 V$	C _L = 15pF C _L = 50pF		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		3.7 5.2	5.5 7.5	1.0 1.0	6.5 8.5	
C _{in}	Input Capacitance				4	10		10	pF

		Typical @ 25°C, V _{CC} = 5.0V	
C _{PD}	Power Dissipation Capacitance (Note 1.)	19	pF

CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

$\textbf{NOISE CHARACTERISTICS} \ (Input \ t_f = t_f = 3.0 ns, \ C_L = 50 pF, \ V_{CC} = 5.0 V, \ Measured \ in \ SOIC \ Package)$

		T _A = 25°C		
Symbol	Characteristic		Max	Unit
VOLP	Quiet Output Maximum Dynamic VOL	0.3	0.8	V
VOLV	Quiet Output Minimum Dynamic V _{OL}	- 0.3	- 0.8	V
VIHD	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V



DEVICE UNDER TEST CL*

* Includes all probe and jig capacitance
Figure 2. Test Circuit

Figure 1. Switching Waveforms

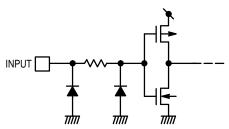
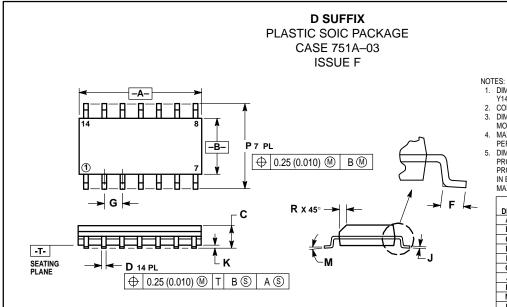


Figure 3. Input Equivalent Circuit

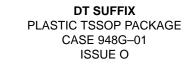
OUTLINE DIMENSIONS

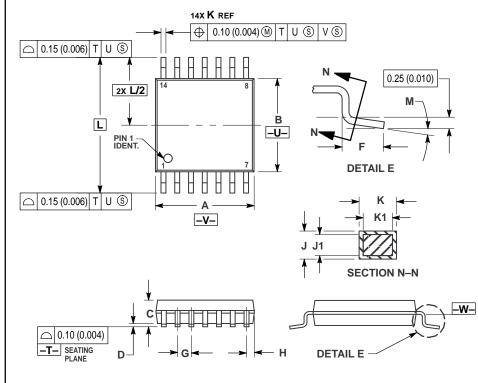


- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- UJUMO) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR
 PROTRUSION SHALL NOT EXCEED
 0.25 (0.010) PER SIDE.
- 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С	_	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

OUTLINE DIMENSIONS

M SUFFIX PLASTIC SOIC EIAJ PACKAGE CASE 965-01 **ISSUE O** Q_1 E HE **DETAIL P** VIEW P 0.13 (0.005) M 0.10 (0.004)

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT, MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	-	2.05		0.081	
Α ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
С	0.18	0.27	0.007	0.011	
D	9.90	10.50	0.390	0.413	
Е	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050 BSC		
ΗE	7.40	8.20	0.291	0.323	
0.50	0.50	0.85	0.020	0.033	
LF	1.10	1.50	0.043	0.059	
М	0 °	10°	0 °	10°	
Q_1	0.70	0.90	0.028	0.035	
Z		1.42		0.056	

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